## 2.5 Summary: Conductors

- What counts are the specific quantities:
  - Conductivity  $\sigma$  (or the specific resistivity  $\rho$  = 1/  $\sigma$
  - · current density *i*
  - (Electrical) field strength E
  - The basic equation for σ is:
     n = concentration of carriers
     μ = mobility of carriers
  - Ohm's law states:
     It is valid for metals, but not for all materials
- $\sigma$  (of conductors / metals) obeys (more or less) several rules; all understandable by looking at n and particularly  $\mu$ .
  - Matthiesen rule
    Reason: Scattering of electrons at defects (including phonons)
    decreases μ.
  - "ρ(7) rule":
     about 0,04 % increase in resistivity per K
     Reason: Scattering of electrons at phonons decreases μ
  - Nordheim's rule:
    Reason: Scattering of electrons at **B** atoms decreases **μ**
- Major consequence: You can't beat the conductivity of pure Ag by "tricks" like alloying or by using other materials. (Not considering superconductors).
- Non-metallic conductors are extremely important.
  - Transparent conductors (TCO's) ("ITO", typically oxides)
  - lonic conductors (liquid and solid)
  - Conductors for high temperature applications; corrosive environments, ..
     (Graphite, Silicides, Nitrides, ...)
  - Organic conductors (and semiconductors)
- Numbers to know (order of magnitude accuracy sufficient)

[ 
$$\sigma$$
] = (  $\Omega$ m)<sup>-1</sup> = S/m;  
S = 1/  $\Omega$  = "Siemens"  
[  $\rho$ ] =  $\Omega$ m

$$\sigma = |q| \cdot n \cdot \mu$$

$$i = \sigma \cdot \mathbf{E}$$

$$\rho = \rho_{\text{Lattice}}(T) + \rho_{\text{defect}}(N)$$

$$\Delta \rho = \alpha_{\rho} \cdot \rho \cdot \Delta T \approx \frac{0.4\%}{^{\circ}C}$$

$$\rho \approx \rho_A + \text{const.} \cdot [B]$$

No flat panels displays = no notebooks etc. without **ITO**!

Batteries, fuel cells, sensors, ...

Example: **MoSi<sub>2</sub>** for heating elements in corrosive environments (dishwasher!).

The future High-Tech key materials?

 $\rho(\text{decent metals}) \text{ about 2 } \mu\Omega\text{cm.} \\ \rho(\text{technical semiconductors}) \\ \text{around 1 } \Omega\text{cm.} \\ \rho(\text{insulators}) > 1 \text{ } G\Omega\text{cm.}$ 

No electrical engineering without conductors! Hundreds of specialized metal alloys exist just for "wires" because besides σ, other demands must be met, too:

Example for unexpected conductors being "best" compromise:

Money, Chemistry (try Na!), Mechanical and Thermal properties, Compatibility with other materials, Compatibility with production technologies, ...

Poly Si, Silicides, **TiN**, **W** in integrated circuits

Contacts (switches, plugs, ...); Resistors; Heating elements; ...

 $j = A \cdot T^2 \cdot \exp{-\frac{E_A}{kT}}$ 

Needs **UHV**!

Essential for measuring (high) temperatures with a "thermoelement" Future use for efficient conversion of heat to electricity ???

Used for electrical cooling of (relatively small) devices. Only big effect if electrical heating ( $\propto P$ ) is small.

**Challenge**: Find / design a material with a "good" ion conductivity at room temperature

 $j_{\text{diff}} = -D \cdot \text{grad}(c)$ 

 $J_{field} = \sigma \cdot E = q \cdot c \cdot \mu \cdot E$ 

Don't forget Special Applications:

- Thermionic emission provides electron beams.
  The electron beam current (density) is given by the Richardson equation:
  - **A**<sub>theo</sub> = 120 A · cm<sup>-2</sup> · K<sup>-2</sup> for free electron gas model  $A_{\text{exp}} \approx (20 160) \text{ A} \cdot \text{cm}^{-2} \cdot \text{K}^{-2}$
  - E<sub>A</sub> = work function ≈ (2 >6) eV
  - Materials of choice: W, LaB<sub>6</sub> single crystal
- High field effects (tunneling, barrier lowering) allow large currents at low **T** from small (nm) size emitter
- There are several thermoelectric effects for metal junctions; always encountered in non-equilibrium.
  - Seebeck effect:
    Thermovoltage develops if a metal A-metal B junction is at a temperature different form the "rest", i.e. if there is a temperature gradeient
  - Peltier effect:

    Electrical current I through a metal metal (or metal semiconductor) junction induces a temperature gradient ∝ I, i.e.
- Electrical current can conducted by ions in

one of the junction may "cool down".

- Liquid electrolytes (like H<sub>2</sub>SO<sub>4</sub> in your "lead acid" car battery); including gels
- Solid electrolytes (= ion-conducting crystals).
   Mandatory for fuel cells and sensors
- Ion beams. Used in (expensive) machinery for "nanoprocessing".
- Basic principle
  - Diffusion current j<sub>diff</sub> driven by concentration gradients grad(c) of the charged particles (= ions here) equilibrates with the
  - Field current jfield caused by the internal field always associated to concentration gradients of charged particles plus the field coming from the outside

Diffusion coefficient D and mobility μ are linked via the Einstein relation;
 concentration c(x) and potential U(x) or field
 E(x) = -dU/dx by the Poisson equation.

$$\mu = eD/kT$$

$$-\frac{d^2U}{dx^2} = \frac{dE}{dx} = \frac{e \cdot c(x)}{\epsilon \epsilon_0}$$

- Immediate results of the equations from above are:
  - In equilibrium we find a preserved quantity, i.e. a quantity independent of x - the electrochemical potential Vec:
  - If you rewrite the equaiton for c(x), it simply asserts that the particles are distributed on the energy scale according to the Boltzmann distrubution:
  - Electrical field gradients and concentration gradients at "contacts" are coupled and non-zero on a length scale given by the Debye length dDebye
  - The Debye length is an extremely important material parameter in "ionics" (akin to the space charge region width in semiconductors); it depends on temperature *T* and in particular on the (bulk) concentration *c*<sub>0</sub> of the (ionic) carriers.
  - The Debye length is not an important material parameter in metals since it is so small that it doesn't matter much.

The potential difference between two materials (her ionic conductors) in close contact thus...

- ... extends over a length given (approximately) by :
- ... is directly given by the Boltzmann distribution written for the energy:
   (with the c<sub>i</sub> =equilibrium conc. far away from the contact.
- The famous Nernst equation, fundamental to ionics, is thus just the Boltzmann distribution in disguise!
- "Ionic" sensors (most famous the **ZrO<sub>2</sub>** based **O<sub>2</sub>** sensor in your car exhaust system) produce a voltage according to the Nernst equation because the concentration of ions on the exposed side depends somehow on the concentration of the species to be measured.

$$V_{\text{ec}} = \text{const.} = e \cdot U(x) + kT \cdot \ln c(x)$$

$$c(x) = \exp{-\frac{(Vx) - V_{ec}}{kT}}$$

$$d_{\text{Debye}} = \left( \frac{\epsilon \cdot \epsilon_0 \cdot kT}{e^2 \cdot c_0} \right)^{1/2}$$

$$d_{\text{Debye}}(1) + d_{\text{Debye}}(2)$$

$$\frac{c_1}{-} = \exp{-\frac{\mathbf{e} \cdot \Delta U}{\mathbf{k}T}}$$

$$\frac{\mathbf{Boltz}}{\mathbf{mann}}$$

$$\Delta U = - \begin{array}{c} kT & c_1 \\ \hline - & \cdot & \ln \frac{c_1}{c_2} \end{array}$$
 Nernst's equation

## **Questionaire**

All multiple choice questions zu 2.
Conductors